

# Amplifier Transistor

## NPN Silicon

# 2N4410

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	80	Vdc
Collector–Base Voltage	$V_{CBO}$	120	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current — Continuous	$I_C$	250	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

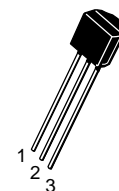
### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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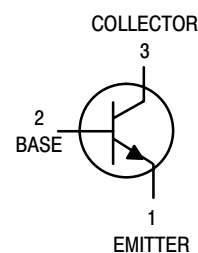
### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CEO}$	80	—	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = 500 \mu\text{Adc}$ , $V_{BE} = 5.0 \text{ Vdc}$ , $R_{BE} = 8.2 \text{ k ohms}$ )	$V_{(BR)CEX}$	120	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	120	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 100 \text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100 \text{ Vdc}$ , $I_E = 0$ , $T_A = 100^\circ\text{C}$ )	$I_{CBO}$	— —	0.01 1.0	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	0.1	$\mu\text{Adc}$

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



CASE 29–11, STYLE 1  
TO–92 (TO–226AA)



## 2N4410

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	60 60	— 400	—
Collector–Emitter Saturation Voltage ( $I_C = 1.0\text{ mA}$ , $I_B = 0.1\text{ mA}$ )	$V_{CE(sat)}$	—	0.2	Vdc
Base–Emitter Saturation Voltage ( $I_C = 1.0\text{ mA}$ , $I_B = 0.1\text{ mA}$ )	$V_{BE(sat)}$	—	0.8	Vdc
Base–Emitter On Voltage ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$V_{BE(on)}$	—	0.8	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product <sup>(2)</sup> ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 20\text{ MHz}$ )	$f_T$	60	300	MHz
Collector–Base Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ , emitter guarded)	$C_{cb}$	—	12	pF
Emitter–Base Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ , collector guarded)	$C_{eb}$	—	50	pF

2.  $f_T = |h_{fe}| \cdot f_{test}$ .

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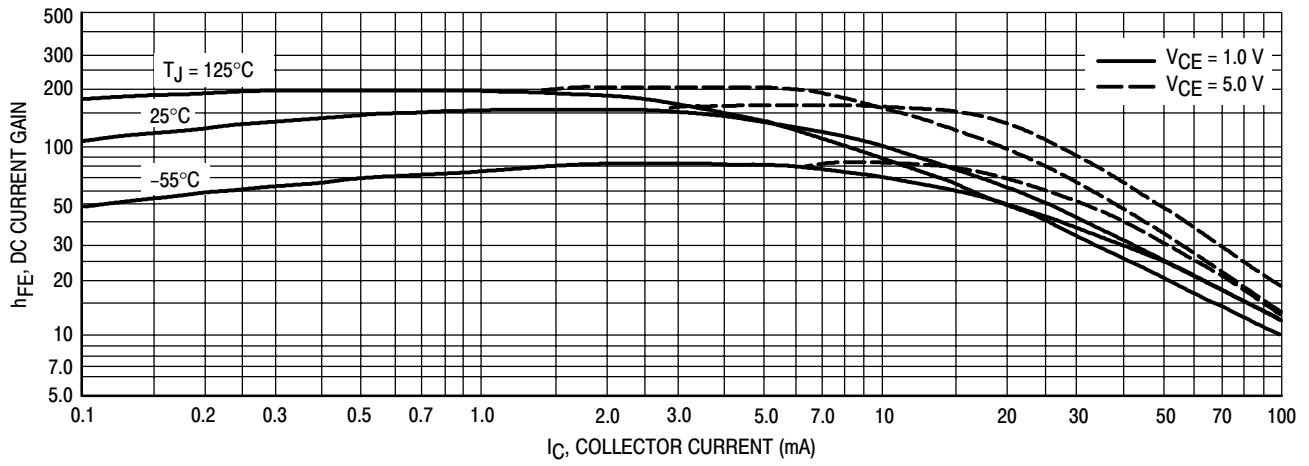


Figure 1. DC Current Gain

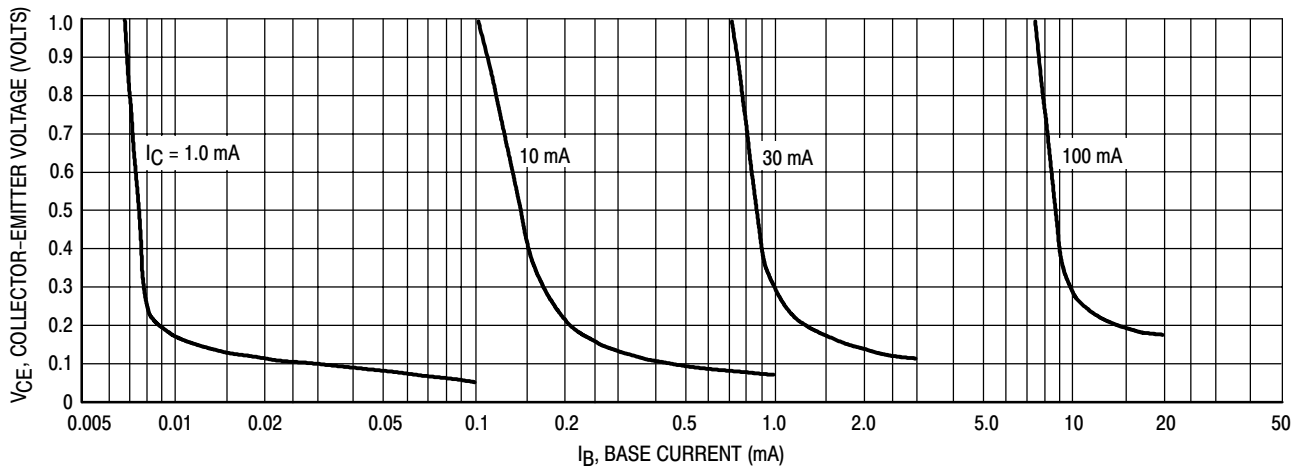


Figure 2. Collector Saturation Region

## 2N4410

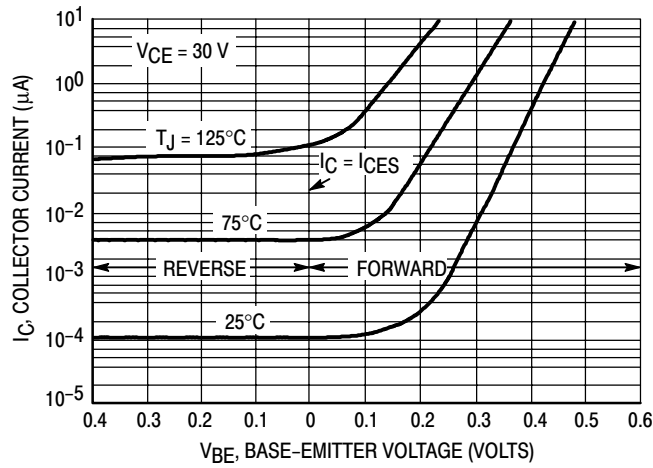


Figure 3. Collector Cut-Off Region

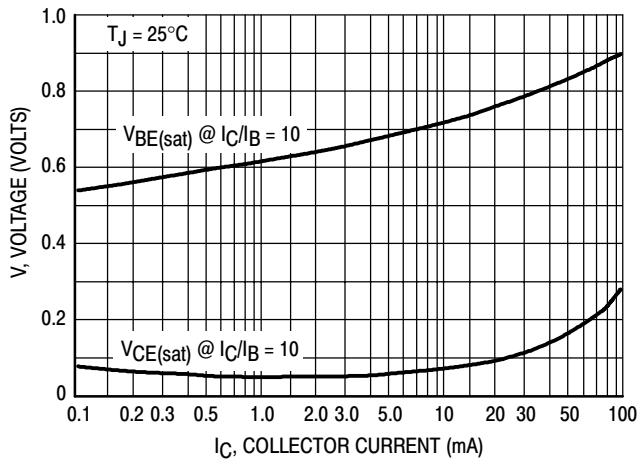


Figure 4. "On" Voltages

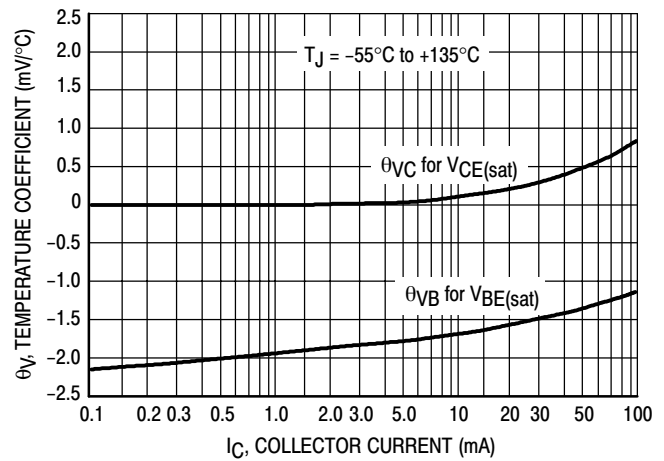


Figure 5. Temperature Coefficients

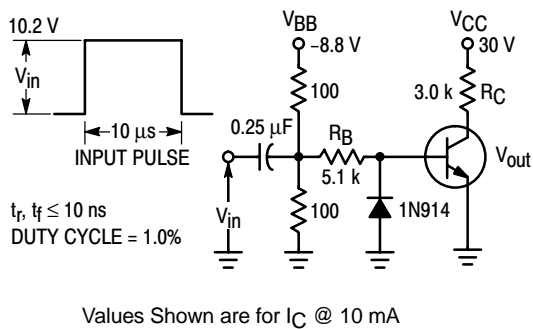


Figure 6. Switching Time Test Circuit

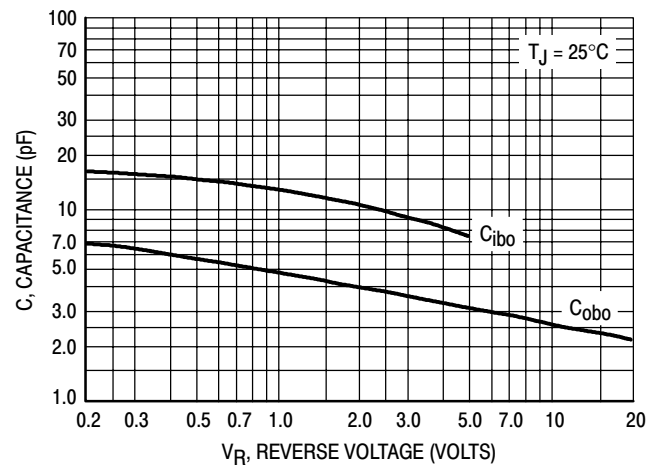


Figure 7. Capacitances

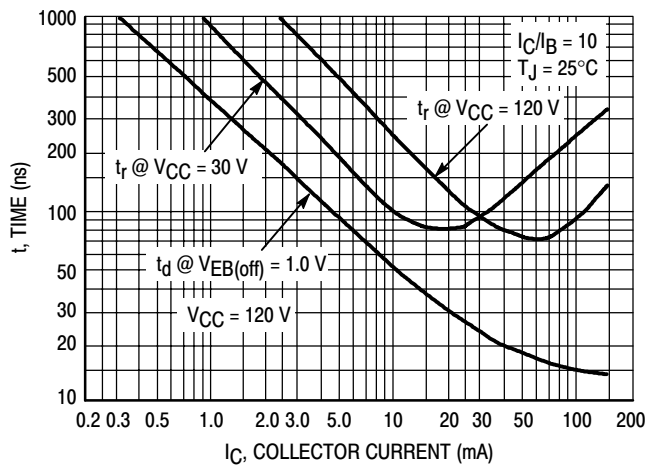


Figure 8. Turn-On Time

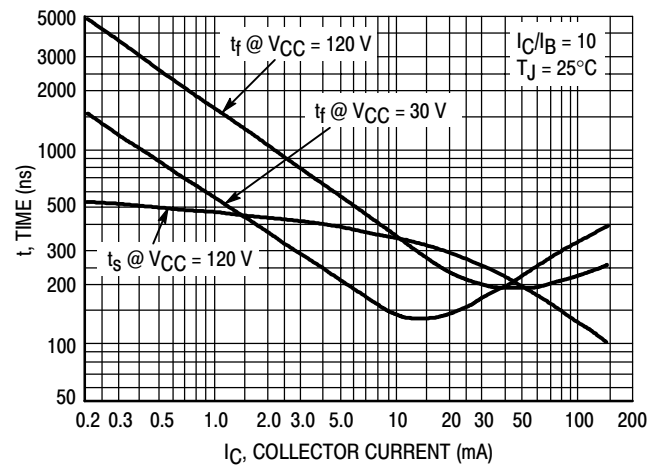
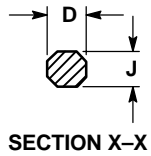
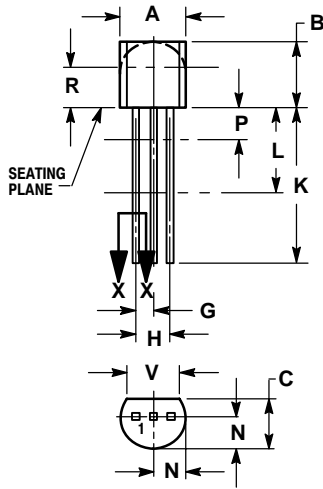


Figure 9. Turn-Off Time

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## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL




STYLE 1:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

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